

HiPerFRED Module

$$V_{RRM} = 1200 \text{ V}$$

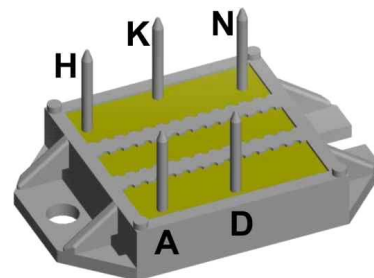
$$I_{DAV} = 24 \text{ A}$$

$$t_{rr} = 40 \text{ ns}$$

Fast Recovery Epitaxial Diode
 Low Loss and Soft Recovery
 3~ Rectifier Bridge

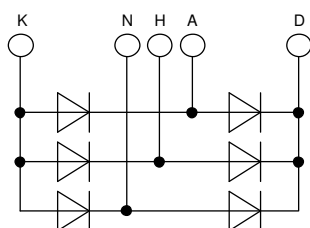
Part number

VUE22-12NO7



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Supplies for DC power equipment
- Input and output rectifiers for high frequency
- Battery DC power supplies
- Field supply for DC motors

Package: ECO-PAC1

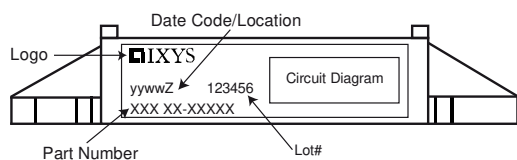
- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V
I _R	reverse current, drain current	V _R = 1200 V	T _{VJ} = 25°C			60	μA
		V _R = 1200 V	T _{VJ} = 150°C			0.25	mA
V _F	forward voltage drop	I _F = 10 A	T _{VJ} = 25°C			2.92	V
		I _F = 30 A				4.05	V
		I _F = 10 A	T _{VJ} = 150°C			1.95	V
		I _F = 30 A				3.02	V
I _{DAV}	bridge output current	T _C = 85°C rectangular d = ⅓	T _{VJ} = 150°C			24	A
V _{F0}	threshold voltage	for power loss calculation only		T _{VJ} = 150°C		1.39	V
r _F	slope resistance					55	mΩ
R _{thJC}	thermal resistance junction to case					2.5	K/W
R _{thCH}	thermal resistance case to heatsink				0.30		K/W
P _{tot}	total power dissipation	T _C = 25°C				50	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		40	A
C _J	junction capacitance	V _R = 600 V f = 1 MHz		T _{VJ} = 25°C	3		pF
I _{RM}	max. reverse recovery current	I _F = 10 A; V _R = 600 V -di _F /dt = 200 A/μs		T _{VJ} = 25 °C	5		A
				T _{VJ} = 100 °C	8		A
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	40		ns
				T _{VJ} = 100 °C	115		ns

Package ECO-PAC1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				19		g
M_D	mounting torque		1.4		2	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	10.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUE22-12NO7	VUE22-12NO7	Box	25	482838

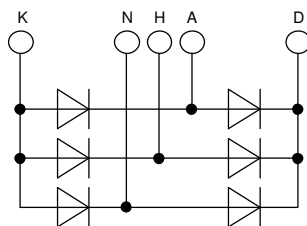
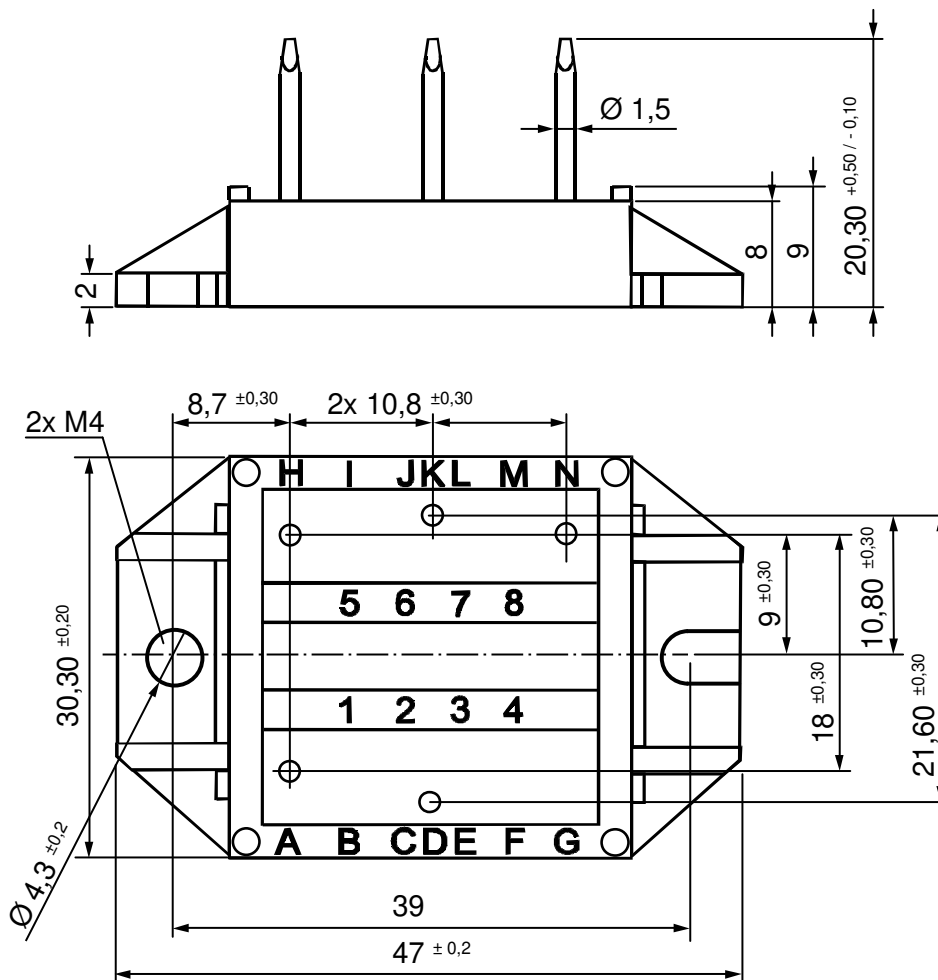
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$

		Fast Diode	
$V_{0\max}$	threshold voltage	1.39	V
$R_{0\max}$	slope resistance *	53	mΩ

Outlines ECO-PAC1



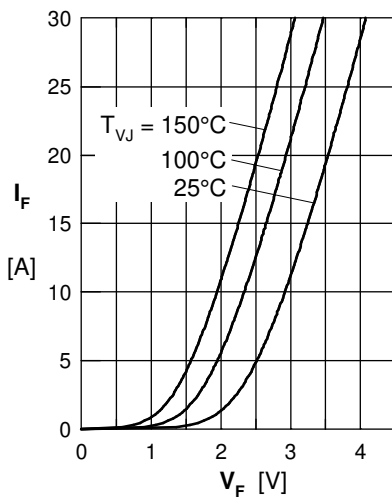
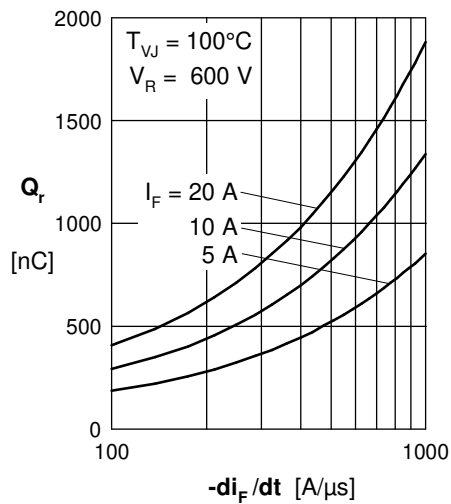
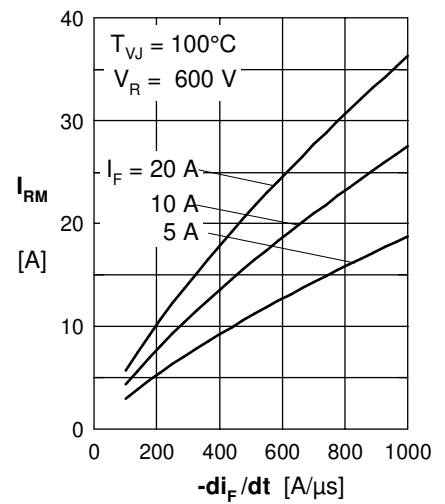
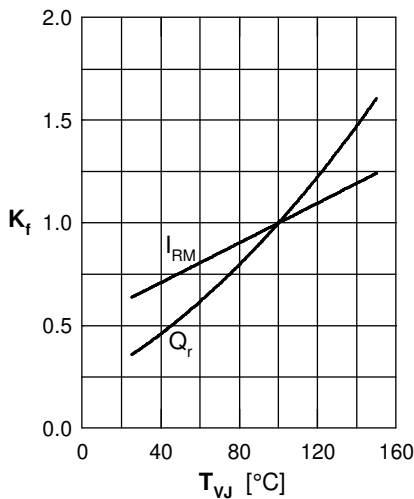
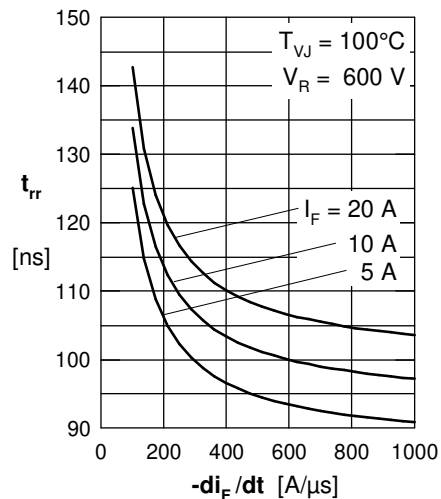
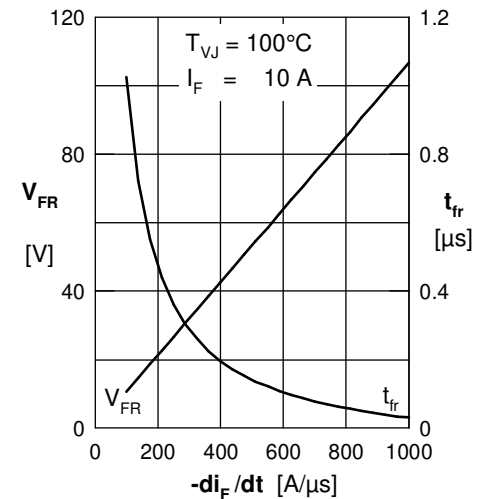
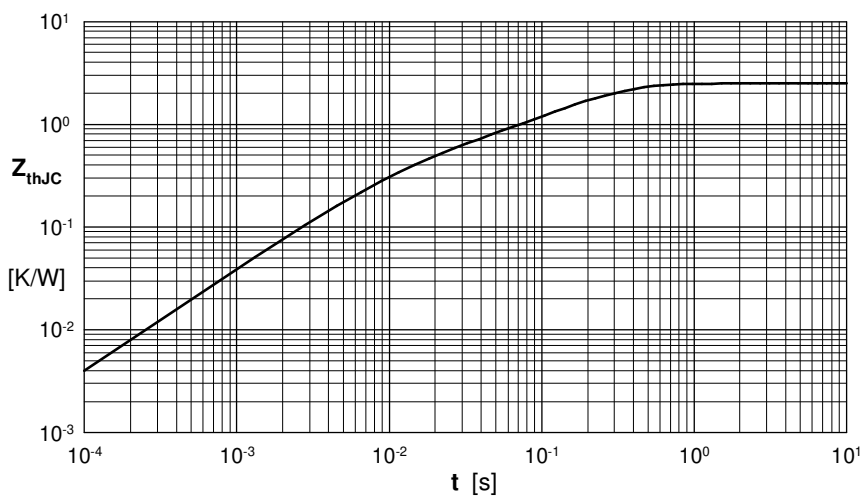
Fast Diode

 Fig. 1 Forward current I_F vs. V_F

 Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

 Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

 Fig. 5 Recovery time t_{rr} vs. $-di_F/dt$

 Fig. 6 Peak forward voltage V_{FR} and t_{fr} vs. $-di_F/dt$


Fig. 7 Transient thermal resistance junction to case

i	R_{thi} (K/W)	t_i (s)
1	0.8776	0.0052
2	0.3378	0.0003
3	0.0678	0.0004
4	1.2168	0.0092